



MIT.9889

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Lee et al.

GROUP: 2811

SERIAL NO: 10/603,712

EXAMINER: Unknown

FILED: 06/25/2003

FOR: A METHOD FOR IMPROVING HOLE MOBILITY ENHANCEMENT IN
STRAINED SILICON P-TYPE MOSFETS

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INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The listed documents were recently cited in a corresponding PCT application, and a copy of the International Search Report is being submitted herewith for purposes of convenience.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that is required.

Respectfully submitted,

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I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the Mail Stop DD, Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Emily C. Porell

02/23/2004

Date

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 STATEMENT BY APPLICANT**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	2002/0052084	05/02/2002	Fitzgerald			05/02/2002
	AB						
	AC						
	AD						
	AE						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AF						
	AG						
	AH						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Channel width dependence of mobility in Ge channel modulation-doped structures," Irisawa et al. <i>Jpn. J. Appl. Phys.</i> April 2001. Vol. 40.
	AJ	"Thermal stability of Ge channel modulation doped structures," Irisawa et al. <i>Journal of Crystal Growth</i> . 2001. Vol. 227-228.
	AK	"Hall mobility enhancement caused by annealing of Si _{0.2} Ge _{0.8} /Si _{0.7} Ge _{0.3} /Si(001) p-type modulation-doped heterostructures," Myronov et al. <i>Applied Physics Letters</i> . May 2002. Vol. 80, No. 19.
	AL	"Quantum mechanical modeling of the charge distribution in a Si/Si _{1-x} Ge _x /Si P-Channel MOSFET," Hargrove et al. <i>Proceedings of the 1994 IEEE International Electron Devices Meeting</i> , San Francisco, CA. December 1994.
	AM	"Characteristics and device design of Sub-100 nm strained Si N- and PMOSFETs," Rim et al. <i>Symposium on VLSI Technology Digest of Technical Papers</i> . 2002.
	AN	"Enhanced performance of strained-Si MOSFETs on CMP SiGe Virtual Substrate," Sugii et al. <i>International Electron Devices Meeting 2001. IEDM. Technical Digest</i> .
	AO	"SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation," Cheng et al. <i>IEEE International SOI Conference</i> . Durango, CO. October 2001.
	AP	"Ultrahigh room-temperature hole hall and effective mobility in Si _{0.3} Ge _{0.7} /Ge/Si _{0.3} Ge _{0.7} heterostructures," Irisawa et al. <i>Applied Physics Letters</i> . July 2002. Vol. 81, No. 5.

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.